

PHN203

Dual N-channel TrenchMOS logic level FET

Rev. 05 — 27 April 2010

Product data sheet

1. Product profile

1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Suitable for high frequency applications due to fast switching characteristics
- Suitable for logic level gate drive sources

1.3 Applications

■ DC-to-DC converters

Lithium-ion battery applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}$		-	-	30	V
I _D	drain current	T _{amb} = 25 °C; pulsed; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	6.3	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; pulsed; see <u>Figure 2</u>	[1]	-	-	2	W
Static char	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>		-	24	30	mΩ
Dynamic c	haracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 7 \text{ A}; V_{DS} = 15 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ Figure 11}}$		-	3	-	nC

^[1] Single device conducting.



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D. D. D. D. D.
2	G1	gate1	8 <u> </u>	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2	1 1 1 1 1 4	
6	D2	drain2	SOT96-1 (SO8)	S1 G1 S2 G2
7	D1	drain1		mbk725
8	D1	drain1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHN203	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	-	30	V
V_{DGR}	drain-gate voltage	$T_j \le 150 ^{\circ}\text{C}; T_j \ge 25 ^{\circ}\text{C}; R_{GS} = 20 \text{k}\Omega$		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	T _{amb} = 70 °C; pulsed; see Figure 1	<u>[1]</u>	-	-	5	Α
		T _{amb} = 25 °C; pulsed; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	6.3	Α
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{amb} = 25 \ ^{\circ}C$; see Figure 3	<u>[1]</u>	-	-	18	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; pulsed; see Figure 2	<u>[1]</u>	-	-	2	W
T _{stg}	storage temperature			-55	-	150	°C
Tj	junction temperature			-55	-	150	°C
Source-drain	diode						
Is	source current	T _{amb} = 25 °C; pulsed	<u>[1]</u>	-	-	2	Α
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{amb} = 25 °C	<u>[1]</u>	-	-	4.1	Α
Avalanche ru	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 8.7 A; $V_{sup} \le$ 30 V; unclamped; t_p = 0.2 ms; R_{GS} = 50 Ω		-	-	37.8	mJ

^[1] Single device conducting.

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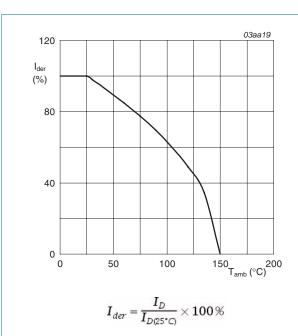


Fig 1. Normalized continuous drain current as a function of ambient temperature

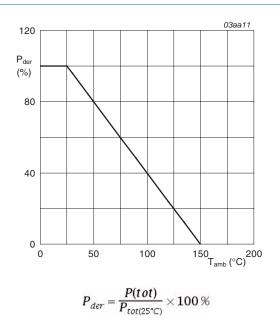
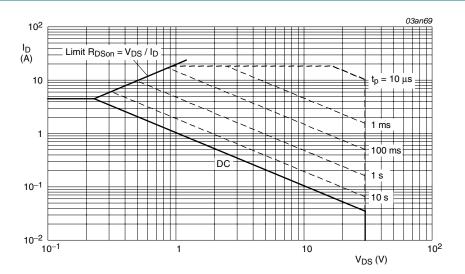


Fig 2. Normalized total power dissipation as a function of ambient temperature



 $T_{amb} = 25$ °C; I_{DM} is single pulse; $V_{GS} = 10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	-	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint; see Figure 4	-	-	62.5	K/W

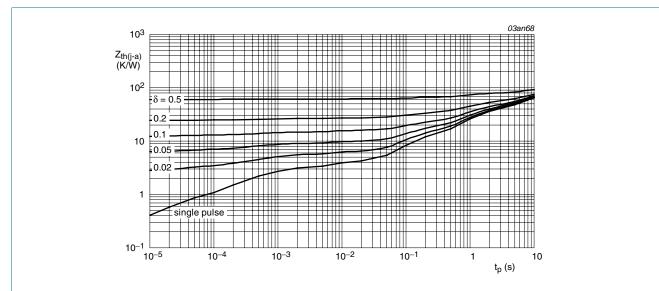


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 8	-	-	2.2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 150$ °C; see <u>Figure 8</u>	0.6	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 8</u>	1	1.5	2	V
I _{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 7 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	24	30	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 3.5 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	30	55	mΩ
		V_{GS} = 10 V; I_D = 7 A; T_j = 150 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	40.8	51	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 7 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$	-	14.6	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	2	-	nC
Q_{GD}	gate-drain charge		-	3	-	nC
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	560	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	125	-	pF
C _{rss}	reverse transfer capacitance	V_{DS} 20 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 12	-	85	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 25 \Omega; V_{GS} = 10 \text{ V};$	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	21	-	ns
t _f	fall time		-	11	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 1.25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 13	-	0.75	1	V
t _{rr}	reverse recovery time	I _S = 2 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 25 V; T _i = 25 °C	-	30	-	ns

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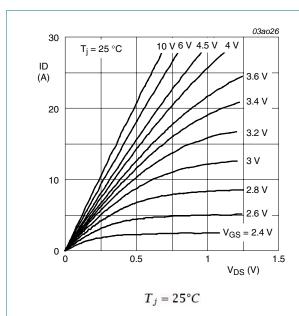


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical value

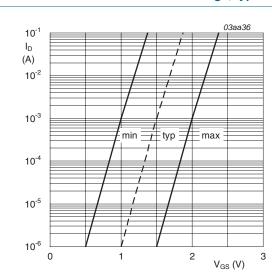
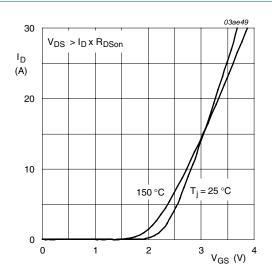


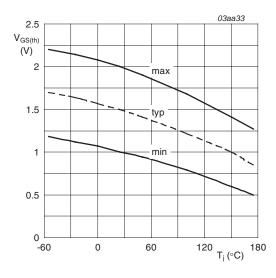
Fig 7. Sub-threshold drain current as a function of gate-source voltage

 $T_j = 25 \,{}^{\circ}C; V_{DS} = V_{GS}$



 $T_j = 25^{\circ}C$ and $150^{\circ}C$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature

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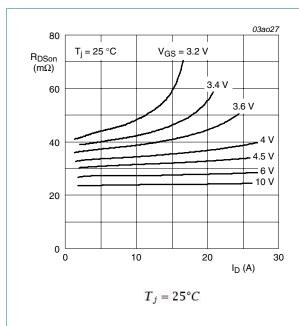


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

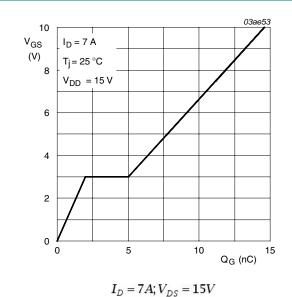


Fig 11. Gate-source voltage as a function of gate charge; typical values

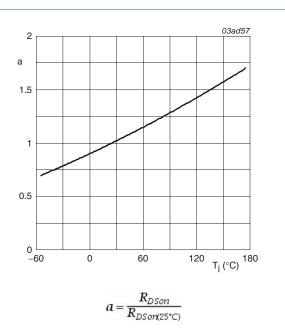
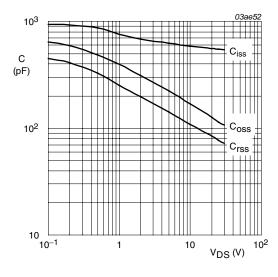


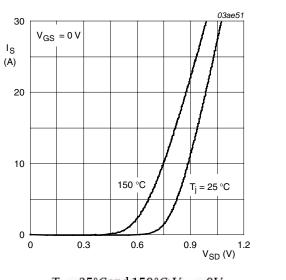
Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



 $V_{GS}=0V; f=1MHz$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 $T_j = 25$ °C and 150°C; $V_{GS} = 0V$

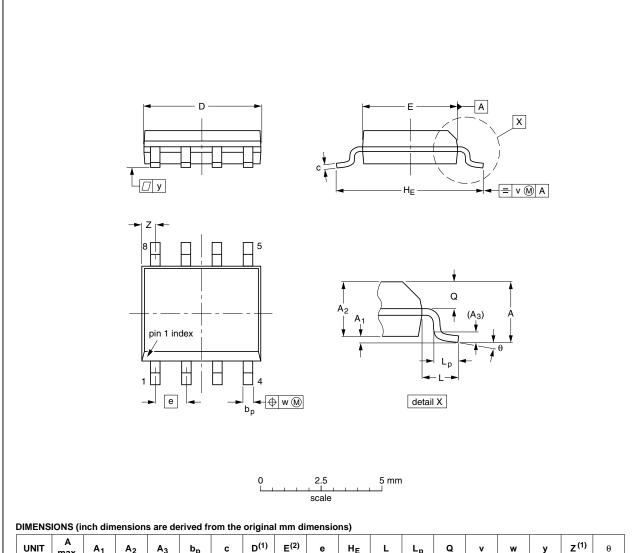
Fig 13. Source current as a function of source-drain voltage; typical values

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7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	σ	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012				99-12-27 03-02-18

Fig 14. Package outline SOT96-1 (SO8)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHN203 _5	20100427	Product data sheet	-	PHN203 _4
Modifications:	 Various cha 	nges to content.		
PHN203 _4	20091208	Product data sheet	-	PHN203-03
PHN203 -03	20040126	Product data	-	PHN203 _2
PHN203_2	19990101	Product specification	-	PHN203 _1
PHN203 _1	19980204	Objective specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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